


<div style="text-align: center;">  <p>INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)</p> </div>	ATTY DOCKET NO. ITL 1063US (P18030)	SERIAL NO. 10/692,696
	APPLICANT(S): Nick Lindert et al.	
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U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Ch	A.	6,214,679	04/10/2001	Murthy et al.		
an	B.	6,342,421	01/29/2002	Mitani et al.		
Ch	C.	6,605,498	08/12/2003	Murthy et al.		
	D.					
	E.					

U.S. PATENT APPLICATION PUBLICATIONS


F.						
G.						
H.						
I.						
J.						

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
Ch	K.	JP 63 013379	06/21/1988	Japan			Abstract Only
an	L.	WO 00/30169	05/25/2000	PCT			
	M.						
	N.						
	O.						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Ch	P.	S. Gannavaram et al., <i>Low Temperature ($\leq 800^{\circ}\text{C}$) Recessed Junction Selective Silicon-Germanium Source/Drain Technology for sub-70 nm CMOS</i> ; International Electron Devices Meeting 2000, IEDM, Technical Digest, San Francisco, CA, Dec. 10-13, 2000, IEEE, US, Dec. 10, 2000, pgs. 437-440.
	Q.	
	R.	
	S.	
	T.	
	U.	

EXAMINER <div style="text-align: center;"></div>	DATE CONSIDERED <div style="text-align: center;">01-05-06</div>
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.